



74LVCH2T45

DUAL BIT DUAL POWER SUPPLY TRANSLATING TRANSCEIVER WITH 3 STATE OUTPUTS

Description

The 74LVCH2T45 is a dual-bit, dual-supply transceiver with tri-state outputs suitable for transmitting two logic bits across different voltage domains. The direction pin (DIR) and Port A, consisting of pins 1A and 2A, have logic levels in relation to V_{CC}(A) while port B, consisting of pins 1B and 2B have logic levels related to V_{CC}(B). This arrangement allows for universal low-voltage translation between any voltages from 1.2V to 5.5V. When a HIGH logic level is applied to the direction pin, port A pins become inputs and port B pins are outputs. Conversely, the roles of the ports are reversed when the direction pin is asserted LOW.

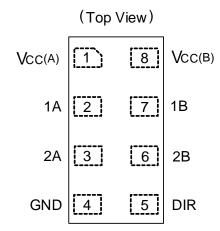
The tri-state (loff) feature places all port pins in a high impedance state when either power supply is at 0V, which prevents and damages backflow currents and provides power-down electrical isolation up to 5.5V as not to interfere with any logic activity on either of the ports.

The 74LVCH2T45 is a variant of the 74LVC2T45 that includes a bus hold feature at each input. The bus hold feature maintains the previous logic level therefore a valid logic level is always present eliminating the need for additional resistors for unused or disconnected inputs.

Features

- Wide Supply Voltage Range:
 - Vcc(A): from 1.2V to 5.5V
 - Vcc(B): from 1.2V to 5.5V
- ± 24mA Output Drive at 3.3V
- CMOS Low Power Consumption 16µA Maximum Icc
- High Noise Immunity
- IOFF Supports Partial-Power-Down Mode Operation
- I_{OFF} Controlled by Either V_{CC} Being at 0V
- Inputs Accept up to 5.5V
- Maximum data rates:
 - 420Mbps (3.3V to 5V translation)
 - 210Mbps (translate to 3.3V)
 - 140Mbps (translate to 2.5V)
 - 75Mbps (translate to 1.8V)
 - 60Mbps (translate to 1.5V)
- ESD Protection Exceeds JESD 22
 - 4000-V Human Body Model (A114)
 - 1000 V Charged Device Model (C101)
- Latch-up Exceeds 100mA per JESD 78, Class I
 Specified from -40°C to +85°C and -40°C to +125°C
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

Pin Assignments



X2-DFN1210-8 X2-DFN1410-8

Applications

- Voltage Level Translation
 Well-Suited to Join Logic Types Operating at Different Voltages
- Power-Down Signal Isolation
 If Either Voltage Domain is Turned Off the Signal is Isolated and
 There is No Loading on Signal Lines
- Wide Array of Products, such as:
 - Cell Phones, Tablets, E-Readers
 - PCs, Notebooks, Netbooks, Ultrabooks
 - Networking, Routers, Gateways
 - Computer Peripherals, Hard Drives, CD/DVD ROM
 - TV, DVD, DVR, Set-Top Box
 - Personal Navigation / GPS
 - MP3 Players, Cameras, Video Recorders

Notes:

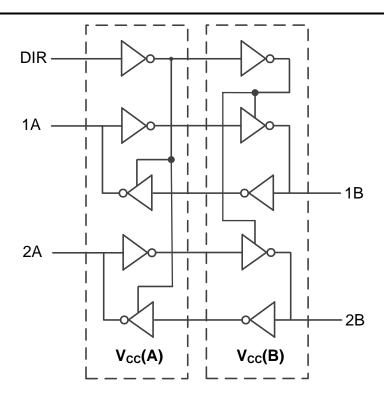
- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.



Pin Descriptions

Pin Name	Pin	Function
VCC(A)	1	Supply for I/O Pin A; Reference for DIR
1A	2	Data Input/Output
2A	3	Data Input/Output
GND	4	Ground
DIR	5	Direction Control
2B	6	Data Input/Output
1B	7	Data Input/Output
VCC(B)	8	Supply for I/O Pin B

Logic Diagram



Function Tables

Input DIR (Direction Pin)	Operation
L	B Data to A Output
Н	A Data to B Output

	Inputs		Outputs		
Α	В	DIR	Α	В	
Note 4	L	L	L	Note 4	
Note 4	Н	L	Н	Note 4	
L	Note 4	Н	Note 4	L	
Н	Note 4	Н	Note 4	Н	

Note: 4. Pin condition not applicable as defined by DIR.



Absolute Maximum Ratings (Note 5) (@TA = +25°C, unless otherwise specified.)

Symbol	Parameter		Rating	Unit
ESD HBM	Human Body Model ESD Protection		4	kV
ESD CDM	Charged Device Model ESD Protection	1	kV	
V _{CC} (A), V _{CC} (B)	Supply Voltage Range		-0.5 to +6.5	V
Vı	Input Voltage Range	-0.5 to +6.5	V	
Vo	Voltage Applied to Output in High Impedance or IOFF	-0.5 to +6.5	V	
V	Voltage Applied to Output in High or Low State	A Pin	-0.3 to V _{CC} (A) +0.5	V
Vo		B Pin	-0.3 to Vcc(B) +0.5	V
lıĸ	Input Clamp Current V _I < 0		-50	mA
Іок	Output Clamp Current		-50	mA
lo	Continuous Output Current		±50	mA
_	Continuous Current Through Vcc or GND	±100	mA	
TJ	Operating Junction Temperature	-40 to +150	°C	
T _{STG}	Storage Temperature		-65 to +150	°C

Note:

Recommended Operating Conditions (Note 6) (@TA = +25°C, unless otherwise specified.)

Symbol	Parameter	Conditions	Min	Max	Unit
Vcc(A)	Supply Voltage A	_	1.2	5.5	V
Vcc(B)	Supply Voltage B	ı	1.2	5.5	V
Vı	Input Voltage	I	0	5.5	V
\/ -	Output Valtage	Active Mode (Note 6)	0	V _{CCO}	V
Vo	Output Voltage	Suspend or 3-State Mode	0	5.5	V
T_A	Ambient Temperature	ı	-40	+125	°C
		Vcci = 1.2V (Note 7)	ı	20	ns/V
		Vcci = 1.4V to 1.95V	ı	20	ns/V
Δt/ΔV	Input Transition Rise and Fall Rate	Vcci = 2.3V to 2.7V	_	20	ns/V
		V _{CCI} = 3V to 3.6V		10	ns/V
		V _{CCI} = 4.5V to 5.5V		5	ns/V

Notes:

^{5.} Stresses beyond the absolute maximum can result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.

^{6.} $\ensuremath{V_{\text{CCO}}}$ is the supply voltage associated with the output port.

^{7.} $\ensuremath{V_{\text{CCI}}}$ is the supply voltage associated with the input port.



Electrical Characteristics (@TA = +25°C.)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{OH}	HIGH-Level Output Voltage	VI = VIH or VIL; IO = -3mA; VCCO = 1.2V	1	1.09	_	٧
V_{OL}	LOW-Level Output Voltage	$V_I = V_{IH}$ or V_{IL} ; $I_O = 3$ mA; $V_{CCO} = 1.2V$	ı	0.07	_	٧
II	Input Leakage Current	DIR Input; $V_1 = 0V$ to 5.5V; $V_{CC1} = 1.2V$ to 5.5V	ı	_	±1	μΑ
I _{BHL}	Bus Hold LOW Current	A or B Port; V _I = 0.42V; V _{CCI} = 1.2V	ı	19	_	μΑ
I _{BHH}	Bus Hold HIGH Current	A or B Port; V _I = 0.78V; V _{CCI} = 1.2V	1	19	_	μΑ
I _{BHLO}	Bus Hold LOW Overdrive Current	A or B Port; Vcci = 1.2V	ı	19	_	μΑ
I _{BHHO}	Bus Hold HIGH Overdrive Current	A or B Port; Vcci = 1.2V	ı	19	_	μΑ
I _{OZ}	OFF-State Output Current	A or B Port; $V_0 = 0V$ or V_{CCO} ; $V_{CCO} = 1.2V$ to 5.5V	-	_	±1	μΑ
	Davier Off Lealings Comment	A Port; V _I or V _O = 0V to 5.5V; V _{CC} (A) = 0V; V _{CC} (B) = 1.2V to 5.5V	_	_	±1	μΑ
l _{OFF}	Power-Off Leakage Current	B Port; V_1 or $V_0 = 0V$ to 5.5V; $V_{CC}(B) = 0V$; $V_{CC}(A) = 1.2V$ to 5.5V	-	_	±1	μΑ
Сі	Input Capacitance	DIR Input; $V_I = 0V$ or 3.3V; $V_{CC}(A) = V_{CC}(B) = 3.3V$		2.2		pF
C _{I/O}	Input/Output Capacitance	A and B Port; Suspend Mode; Vo = 3.3V or 0V; V _{CC(A)} = V _{CC(B)} = 3.3V	-	6.0	_	pF

Electrical Characteristics (continued) (@T_A = +25°C.)

0	Danamatan	O-milition -	-40°C	to +85°C	-40°C	to +125°C	1114
Symbol	Parameter	Conditions	Min	Max	Min	Max	Unit
		Data Input					
		Vcci = 1.2V	0.8Vccı	1	0.8Vccı		V
		Vcci = 1.4V to 1.95V	0.65Vccı	_	0.65Vccı		V
		V _{CCI} = 2.3V to 2.7V	1.7	_	1.7	_	V
		V _{CCI} = 3.0V to 3.6V	2.0	_	2.0	_	V
\/	HIGH-Level	Vcci = 4.5V to 5.5V	0.7Vccı	_	0.7Vccı	_	V
V_{IH}	Input Voltage	DIR Input					
		Vcci = 1.2V	0.8V _{CC} (A)	_	0.8V _{CC} (A)		V
		Vcci = 1.4V to 1.95V	0.65Vcc(A)	_	0.65Vcc(A)		V
		Vcci = 2.3V to 2.7V	1.7	_	1.7		V
		Vcci = 3.0V to 3.6V	2.0	1	2.0		V
		V _{CCI} = 4.5V to 5.5V	0.7Vcc(A)	_	0.7Vcc(A)		V
		Data Input					
		Vcci = 1.2V	_	0.2Vccı	_	0.2Vccı	V
\/	LOW-Level Input	V _{CCI} = 1.4V to 1.95V	_	0.35V _{CCI}	_	0.35V _{CCI}	V
V_{IL}	Voltage	Vcci = 2.3V to 2.7V	_	0.7	_	0.7	V
		Vcci = 3.0V to 3.6V	_	0.8	_	0.8	V
		Vcci = 4.5V to 5.5V	_	0.3Vccı	_	0.3Vccı	V



Electrical Characteristics (continued) (@TA = +25°C.)

0	B	O and distance	-40°C	C to +85°C	-40°C	l lni4	
Symbol	Parameter	Conditions	Min	Max	Min	Max	Unit
		DIR Input	<u>.</u>				
	LOW-Level Input	Vcci = 1.2V	_	0.2V _{CC} (A)	_	0.2V _{CC} (A)	V
V_{IL}		Vcci = 1.4V to 1.95V	_	0.35Vcc(A)	_	0.35Vcc(A)	V
۷IL	Voltage	V _{CCI} = 2.3V to 2.7V	_	0.7	1	0.7	V
		V _{CCI} = 3.0V to 3.6V	_	0.8		0.8	V
		V _{CCI} = 4.5V to 5.5V	_	0.3Vcc(A)	_	0.3Vcc(A)	V
		$V_I = V_{IH}$					
		I _O = -100μA V _{CCO} = 1.2V to 4.5V	Vcco - 0.1	_	Vcco - 0.1	_	V
.,	HIGH-Level	Io = -6mA; Vcco = 1.4V	1.0	_	1.0	_	V
V_{OH}	Output Voltage	Io = -8mA; Vcco = 1.65V	1.2	_	1.2	_	V
		Io = -12mA; Vcco = 2.3V	1.9	_	1.9	_	V
		Io = -24mA; Vcco = 3.0V	2.4	_	2.4	_	V
		Io = -32mA; Vcco = 4.5V	3.8	_	3.8	_	V
	LOW-Level Output Voltage	$V_{I} = V_{IL}$					
		I _O = 100μA; V _{CCO} = 1.2V to 4.5V	_	0.1	_	0.1	V
.,		Io = 6mA; Vcco = 1.4V	_	0.3	1	0.3	V
V_{OL}		I _O = 8mA; V _{CCO} = 1.65V	_	0.45	1	0.45	V
		$I_{O} = 12mA; V_{CCO} = 2.3V$	_	0.3	1	0.3	V
		Io = 24mA; Vcco = 3.0V	_	0.55	_	0.55	V
		Io = 32mA; Vcco = 4.5V		0.55	_	0.55	V
lı	Input Leakage Current	DIR Input; $V_1 = 0V$ to 5.5V; $V_{CCI} = 1.2V$ to 5.5V	_	±2	_	±10	μA
loz	OFF-State Output Current	A or B Port; Vo = 0V or Vcco; Vcco = 1.2V to 5.5V	_	±2	_	±10	μA
		A or B Port					
		V _I = 0.49V; V _{CCI} = 1.4V	15	_	10	_	μA
I	Bus Hold LOW	V _I = 0.58V; V _{CCI} = 1.65V	25	_	20	_	μΑ
I _{BHL}	Current	V _I = 0.70V; V _{CCI} = 2.3V	45	_	45	_	μΑ
		V _I = 0.80V; V _{CCI} = 3.0V	100	_	80	_	μΑ
		V _I = 1.35V; V _{CCI} = 4.5V	100	_	100	_	μΑ
		A or B Port	I			l	
		V _I = 0.91V; V _{CCI} = 1.4V	-15	_	-10	_	μA
	Bus Hold HIGH	V _I = 1.07V; V _{CCI} = 1.65V	-25	_	-20	_	μΑ
I _{BHH}	Current	V _I = 1.60V; V _{CCI} = 2.3V	-45	_	-45	_	μA
		V _I = 2.00V; V _{CCI} = 3.0V	-100	_	-80	_	μA
		V _I = 3.15V; V _{CCI} = 4.5V	-100	_	-100	_	μA



Electrical Characteristics (continued) (@TA = +25°C.)

0	B	O - wild - w -	-40°C	to +85°C	-40°C	to +125°C	1114
Symbol	Parameter	Conditions	Min	Max	Min	Max	Unit
		A or B Port					
		V _{CCI} = 1.6V	125	_	125	_	μΑ
	Bus Hold LOW	V _{CCI} = 1.95V	200	_	200	_	μA
I _{BHLO}	Overdrive Current	Vcci = 2.7V	300	_	300	_	μΑ
		V _{CCI} = 3.6V	500	_	500	_	μΑ
		V _{CCI} = 5.5V	900	_	900	_	μA
		A or B port	l	l			
		Vcci = 1.6V	-125	_	-125	_	μΑ
l.	Bus Hold HIGH	V _{CCI} = 1.95V	-200	_	-200	_	μΑ
Івнно	Overdrive Current	V _{CCI} = 2.7V	-300	_	-300	_	μΑ
		Vcci = 3.6V	-500	_	-500	_	μA
		V _{CCI} = 5.5V	-900	_	-900	_	μΑ
	Power-Off Leakage	A Port; V_1 or $V_0 = 0V$ to 5.5V; $V_{CC}(A) = 0V$; $V_{CC}(B) = 1.2V$ to 5.5V	_	±2	_	±10	μΑ
loff	Current	B Port; V_1 or $V_0 = 0V$ to 5.5V; $V_{CC}(B) = 0V$; $V_{CC}(A) = 1.2V$ to 5.5V	_	±2	_	±10	μΑ
		A Port; $V_I = 0V$ or V_{CCI} ; $I_O = 0A$	_	_	_	_	_
		$V_{CC}(A)$, $V_{CC}(B) = 1.2V$ to 5.5V	_	8	_	8	μΑ
		$V_{CC}(A)$, $V_{CC}(B) = 1.65V$ to 5.5V	_	3	_	3	μA
		$V_{CC}(A) = 5.5V ; V_{CC}(B) = 0V$	_	2		2	μA
		$V_{CC}(A) = 0V ; V_{CC}(B) = 5.5V$	-2	_	-2	_	μΑ
		B Port; $V_I = 0V$ or V_{CCI} ; $I_O = 0A$	_	_	_	_	_
Icc	Supply Current	$V_{CC}(A)_{,} V_{CC}(B) = 1.2V \text{ to } 5.5V$	_	8	_	8	μΑ
		$V_{CC}(A)_{,} V_{CC}(B) = 1.65V \text{ to } 5.5V$	_	3	_	3	μΑ
		$V_{CC}(A) = 5.5V ; V_{CC}(B) = 0V$	-2	_	-2	_	μΑ
		Vcc(A) = 0V ; Vcc(B) = 5.5V	_	2	_	2	μA
		A Plus B Port ($I_{CC(A)} + I_{CC(B)}$); $I_0 = 0A$; $V_1 = 0V$ or V_{CC1}	_	_	_	_	_
		$V_{CC}(A)$, $V_{CC}(B) = 1.2V$ to 5.5V	_	16	_	16	μΑ
		$V_{CC}(A)$, $V_{CC}(B) = 1.65V$ to 5.5V	_	4	_	4	μA



Package Characteristics (V_{CC} = 3.3V, T_A = +25°C, unless otherwise specified.)

Symbol	Parameter	Package	Test Conditions	Min	Тур	Max	Unit
	Thermal Resistance Junction-	X2-DFN1210-8	Note 8	1	295	1	°C/W
	to-Ambient	X2-DFN1410-8	Note o		133		
0	Thermal Resistance Junction-	X2-DFN1210-8	Note 8	_	280	_	°C / / /
Θ \circ	to-Case	X2-DFN1410-8	Note o		127	_	°C/W

Note: 8. Test condition for X2- DFN1210-8 and X2- DFN1410-8: Device mounted on FR-4 substrate PCB, 2oz copper with minimum recommended pad layout.

Switching Characteristics (V_{CC} (A) = 1.2V, T_A = +25°C, see Figure 1)

Parameter	From	То	Vcc(B) = 1.2V	Vcc(B) = 1.5V	Vcc(B) = 1.8V	Vcc(B) = 2.5V	Vcc(B) = 3.3V	Vcc(B) = 5V	Unit
rarameter	(Input)	(Output)	Тур	Тур	Тур	Тур	Тур	Тур	Onne
4	Α	В	10.6	8.1	7.0	5.8	5.3	5.1	no
t _{pLH}	В	Α	10.6	9.5	9.0	8.5	8.3	8.2	ns
4	Α	В	10.1	7.1	6.0	5.3	5.2	5.4	no
t _{pHL}	В	Α	10.1	8.6	8.1	7.8	7.6	7.6	ns
4	DIR	Α	9.4	9.4	9.4	9.4	9.4	9.4	ns
t _{pHZ}	DIR	В	12.0	9.4	9.0	7.8	8.4	7.9	
4	DIR	Α	7.1	7.1	7.1	7.1	7.1	7.1	no
t _{pLZ}	DIR	В	9.5	7.8	7.7	6.9	7.6	7.0	ns
4	DIR	Α	20.1	17.3	16.7	15.4	15.9	15.2	
tpZH	DIR	В	17.7	15.2	14.1	12.9	12.4	12.2	ns
4	DIR	Α	22.1	18.0	17.1	15.6	16.0	15.5	20
t _{pZL}	DIR	В	19.5	16.5	15.4	14.7	14.6	14.8	ns



Switching Characteristics (Vcc (B) = 1.2V, TA = 25°C, see Figure 1)

Parameter	From	То	Vcc(A) = 1.2V	Vcc(A) = 1.5V	Vcc(A) = 1.8V	Vcc(A) = 2.5V	Vcc(A) = 3.3V	Vcc(A) = 5V	Unit
Farameter	(Input)	(Output)	Тур	Тур	Тур	Тур	Тур	Тур	Joint
4	Α	В	10.6	9.5	9.0	8.5	8.3	8.2	ns
t _{pLH}	В	Α	10.6	8.1	7.0	5.8	5.3	5.1	115
4	Α	В	10.1	8.6	8.1	7.8	7.6	7.6	
t _{pHL}	В	Α	10.1	7.1	6.0	5.3	5.2	5.4	ns
4	DIR	Α	9.4	6.5	5.7	4.1	4.1	3.0	ns
t _{pHZ}	DIR	В	12.0	6.1	5.4	4.6	4.3	4.0	
4	DIR	Α	7.1	4.9	4.5	3.2	3.4	2.5	ns
t _{pLZ}	DIR	В	9.5	7.3	6.6	5.9	5.7	5.6	115
4	DIR	Α	20.1	15.4	13.6	11.7	11.0	10.7	
tpZH	DIR	В	17.7	14.4	13.5	11.7	11.7	10.7	ns
4	DIR	Α	22.1	13.2	11.4	9.9	9.5	9.4	20
t _{pZL}	DIR	В	19.5	15.1	13.8	11.9	11.7	10.6	ns

Switching Characteristics (V_{CC} (A) = 1.5V \pm 0.1V, T_A = -40°C to +85°C, see Figure 1)

Parameter	From (Input)	To (Output)	,	= 1.5V .1V	,) = 1.8V .15V	•) = 2.5V 0.2V) = 3.3V).3V	•	3) = 5V 0.5V	Unit
	(iliput)	(Output)	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
4	Α	В	2.8	21.3	2.4	17.6	2.0	13.5	1.7	11.8	1.6	10.5	20
t _{pLH}	В	Α	2.8	21.3	2.6	19.1	2.3	14.9	2.3	12.4	2.2	12.0	ns
4	Α	В	2.6	19.3	2.2	15.3	1.8	11.8	1.7	10.9	1.7	10.8	
tpHL	В	Α	2.6	19.3	2.4	17.3	2.3	13.2	2.2	11.3	2.3	11.0	ns
	DIR	Α	3.0	18.7	3.0	18.7	3.0	18.7	3.0	18.7	3.0	18.7	
t _{pHZ}	DIR	В	3.5	24.8	3.5	23.6	3.0	11.0	3.3	11.3	2.8	10.3	ns
4	DIR	Α	2.4	11.4	2.4	11.4	2.4	11.4	2.4	11.4	2.4	11.4	20
t _{pLZ}	DIR	В	2.8	18.3	3.0	17.2	2.5	9.4	3.0	10.1	2.5	9.4	ns
4	DIR	Α	_	39.6	_	36.3	_	24.3	_	22.5	_	21.4	
tpZH	DIR	В	_	32.7	_	29.0	_	24.9	_	23.2	_	21.9	ns
4	DIR	Α	_	44.1	_	40.9	_	24.2	_	22.6	_	21.3	no
t _{pZL}	DIR	В	_	38.0	_	34.0	_	30.5	_	29.6	_	29.5	ns

Switching Characteristics (continued) (V_{CC} (A) = 1.8V \pm 0.15V, T_A = -40°C to +85°C, see Figure 1)

Parameter	From (Input)	To (Output)		= 1.5V .1V) = 1.8V .15V) = 2.5V 0.2V) = 3.3V).3V		3) = 5V).5V	Unit
	(Iliput)	(Output)	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
4	Α	В	2.6	19.1	2.2	17.7	2.2	9.3	1.7	7.2	1.4	6.8	20
t _{pLH}	В	Α	2.4	17.6	2.2	17.7	2.3	16.0	2.1	15.5	1.9	15.1	ns
4	Α	В	2.4	17.3	2.0	14.3	1.6	8.5	1.8	7.1	1.7	7.0	20
t _{pHL}	В	Α	2.2	15.3	2.0	14.3	2.1	12.9	2.0	12.6	1.8	12.2	ns
4	DIR	Α	2.9	17.1	2.9	17.1	2.9	17.1	2.9	17.1	2.9	17.1	20
tpHZ	DIR	В	3.2	24.1	3.2	21.9	2.7	11.5	3.0	10.3	2.5	8.2	ns
. . –	DIR	Α	2.4	10.5	2.4	10.5	2.4	10.5	2.4	10.5	2.4	10.5	20
t _{pLZ}	DIR	В	2.5	17.6	2.6	16.0	2.2	9.2	2.7	8.4	2.4	7.1	ns
4	DIR	Α	_	35.2	_	33.7	_	25.2	_	23.9	_	22.2	20
tpZH	DIR	В	_	29.6	_	28.2	_	19.8	_	17.7	_	17.3	ns
4	DIR	Α	_	39.4	_	36.2	_	24.4	_	22.9	_	20.4	no
t _{pZL}	DIR	В	_	34.4	_	31.4	_	25.6	_	24.2	_	24.1	ns



Switching Characteristics (continued) (V_{CC} (A) = 2.5V \pm 0.2V, T_{A} = -40°C to +85°C, see Figure 1)

Parameter	From (Input)	To (Output)		= 1.5V .1V) = 1.8V .15V	•) = 2.5V 0.2V	` ') = 3.3V).3V		3) = 5V 0.5V	Unit
	(IIIput)	(Output)	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
4	А	В	2.3	17.9	2.3	16.0	1.5	8.5	1.3	6.2	1.1	4.8	20
t _{pLH}	В	Α	2.0	13.5	2.2	9.3	1.5	8.5	1.4	8.0	1.0	7.5	ns
4	А	В	2.3	15.8	2.1	12.9	1.4	7.5	1.3	5.4	0.9	4.6	
t _{pHL}	В	Α	1.8	11.8	1.9	8.5	1.4	7.5	1.3	7.0	0.9	6.2	ns
t-117	DIR	Α	2.1	8.1	2.1	8.1	2.1	8.1	2.1	8.1	2.1	8.1	
t _{pHZ}	DIR	В	3.0	22.5	3.0	21.4	2.5	11.0	2.8	9.3	2.3	6.9	ns
4	DIR	Α	1.7	5.8	1.7	5.8	1.7	5.8	1.7	5.8	1.7	5.8	
t _{pLZ}	DIR	В	2.3	14.6	2.5	13.2	2.0	9.0	2.5	8.4	1.8	5.8	ns
	DIR	Α	_	28.1	_	22.5	_	17.5	_	16.4	_	13.3	
t _p zH	DIR	В	_	23.7	_	21.8	_	14.3	_	12.0	_	10.6	ns
1	DIR	Α	_	34.3	_	29.9	_	18.5	_	16.3	_	13.1	
t _{pZL}	DIR	В	_	23.9	_	21.0	_	15.6	_	13.5	_	12.7	ns

Switching Characteristics (continued) (V_{CC} (A) = 3.3V \pm 0.3V, T_{A} = -40°C to +85°C, see Figure 1)

Parameter	From (Input)	To (Output)		= 1.5V .1V) = 1.8V .15V) = 2.5V 0.2V) = 3.3V).3V		3) = 5V 0.5V	Unit
	(iliput)	(Output)	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
4	Α	В	2.3	17.1	2.1	15.5	1.4	8.0	0.8	5.6	0.7	4.4	no
t _{pLH}	В	Α	1.7	11.8	1.7	7.2	1.3	6.2	0.7	5.6	0.6	5.4	ns
4	Α	В	2.2	15.6	2.0	12.6	1.3	7.0	0.8	5.0	0.7	4.0	
t _{pHL}	В	Α	1.7	10.9	1.8	7.1	1.3	5.4	0.8	5.0	0.7	4.5	ns
4	DIR	Α	2.3	7.3	2.3	7.3	2.3	7.3	2.3	7.3	2.7	7.3	
t _{pHZ}	DIR	В	2.9	18.0	2.9	16.5	2.3	10.1	2.7	8.6	2.2	6.3	ns
	DIR	Α	2.0	5.6	2.0	5.6	2.0	5.6	2.0	5.6	2.0	5.6	
t _{pLZ}	DIR	В	2.3	13.6	2.4	12.5	1.9	7.8	2.3	7.1	1.7	4.9	ns
	DIR	Α	_	25.4	_	19.7	_	14.0	_	12.7	_	10.3	
t _{pZH}	DIR	В	_	22.7	_	21.1	_	13.6	_	11.2	_	10.0	ns
	DIR	Α	_	28.9	_	23.6	_	15.5	_	13.6	_	10.8	
t pZL	DIR	В	_	22.9	_	19.9	_	14.3	_	12.3	_	11.3	ns

Switching Characteristics (continued) (V_{CC} (A) = 5.0V ± 0.5V, T_{A} = -40°C to +85°C, see Figure 1)

Parameter	From (Input)	To (Output)		= 1.5V .1V		= 1.8V 15V) = 2.5V 0.2V) = 3.3V).3V		3) = 5V 3.5V	Unit
	(iliput)	(Output)	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
4	Α	В	2.2	16.6	1.9	15.1	1.0	7.5	0.7	5.4	0.5	3.9	20
t _{pLH}	В	Α	1.6	10.5	1.4	6.8	1.0	4.8	0.7	4.4	0.5	3.9	ns
4	Α	В	2.3	15.3	1.8	12.2	1.0	6.2	0.7	4.5	0.5	3.5	20
t _{pHL}	В	Α	1.7	10.8	1.7	7.0	0.9	4.6	0.7	4.0	0.5	3.5	ns
4	DIR	Α	1.7	5.4	1.7	5.4	1.7	5.4	1.7	5.4	1.7	5.4	20
t _{pHZ}	DIR	В	2.9	17.3	2.9	16.1	2.3	9.7	2.7	8.0	2.5	5.7	ns
.	DIR	Α	1.4	3.7	1.4	3.7	1.3	3.7	1.0	3.7	0.9	3.7	ns
t _{pLZ}	DIR	В	2.3	13.1	2.4	12.1	1.9	7.4	2.3	7.0	1.8	4.5	115
4	DIR	Α	_	23.6	_	18.9	_	12.2	_	11.4	_	8.4	ns
t _{pZH}	DIR	В	_	20.3	_	18.8	_	11.2	_	9.1	_	7.6	115
.	DIR	Α	-	28.1	_	23.1	_	14.3	_	12.0	1	9.2	20
t pZL	DIR	В	_	20.7	_	17.6	_	11.6	_	9.9	_	8.9	ns



Switching Characteristics (continued) (V_{CC} (A) = 1.5V \pm 0.1V, T_A = -40°C to +125°C, see Figure 1)

Parameter	From (Input)	To (Output)		= 1.5V .1V) = 1.8V .15V	•) = 2.5V 0.2V	` ') = 3.3V).3V		3) = 5V).5V	Unit
	(Iliput)	(Output)	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
4	Α	В	2.5	23.5	2.1	19.4	1.8	14.9	1.5	13.0	1.4	11.6	ns
t _{pLH}	В	Α	2.5	23.5	2.3	21.1	2.0	16.4	2.0	13.7	1.9	13.2	115
4	Α	В	2.3	21.3	1.9	16.9	1.6	13.0	1.5	12.0	1.5	11.9	20
t _{pHL}	В	Α	2.3	21.3	2.1	19.1	2.0	14.6	1.9	12.5	2.0	12.1	ns
4	DIR	Α	2.7	20.6	2.7	20.6	2.7	20.6	2.7	20.6	2.7	20.6	no
t _{pHZ}	DIR	В	3.1	27.3	3.1	26.0	2.7	12.1	2.9	12.5	2.5	11.4	ns
4	DIR	Α	2.1	12.6	2.1	12.6	2.1	12.6	2.1	12.6	2.1	12.6	ns
t _{pLZ}	DIR	В	2.5	20.2	2.7	19.0	2.2	10.4	2.7	11.2	2.2	10.4	115
4	DIR	Α	_	43.7	_	40.1	_	26.8	_	24.9	_	23.6	20
tpZH	DIR	В	_	36.1	_	32.0	_	27.5	_	25.6	_	24.2	ns
4	DIR	Α	_	48.6	_	45.1	_	26.7	_	25.0	_	23.5	200
t _{pZL}	DIR	В	_	41.9	_	37.5	_	33.6	_	32.6	_	32.5	ns

Switching Characteristics (continued) (V_{CC} (A) = 1.8V \pm 0.15V, T_A = -40°C to +125°C, see Figure 1)

Parameter	From (Input)	To (Output)		= 1.5V .1V		= 1.8V 15V) = 2.5V).2V) = 3.3V).3V		3) = 5V 3.5V	Unit
	(iliput)	(Output)	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
4	Α	В	2.3	21.1	1.9	19.5	1.9	10.3	1.5	8.0	1.2	7.5	ns
t _{pLH}	В	Α	2.1	19.4	1.9	19.5	2.0	17.6	1.8	17.1	1.7	16.7	115
4	Α	В	2.1	19.1	1.8	15.8	1.4	9.4	1.6	7.9	1.5	7.7	20
tpHL	В	Α	1.9	16.9	1.8	15.8	1.8	14.2	1.8	13.9	1.6	13.5	ns
t	DIR	Α	2.6	18.9	2.6	18.9	2.6	18.9	2.6	18.9	2.6	18.9	5
t _{pHZ}	DIR	В	2.8	26.6	2.8	24.1	2.4	12.7	2.7	11.4	2.2	9.1	ns
4	DIR	Α	2.1	11.6	2.1	11.6	2.1	11.6	2.1	11.6	2.1	11.6	20
t _{pLZ}	DIR	В	2.2	19.4	2.3	17.6	1.9	10.2	2.4	9.3	2.1	7.9	ns
4	DIR	Α	_	38.8	_	37.1	_	27.8	_	26.4	_	24.6	20
t _р zн	DIR	В	_	32.7	_	31.1	_	21.9	_	19.6	_	19.1	ns
4	DIR	Α	_	43.5	_	39.9	_	26.9	_	25.3	_	22.6	no
t _{pZL}	DIR	В	_	38.0	_	34.7		28.3	_	26.8	_	26.6	ns

Switching Characteristics (continued) (VCC (A) = 2.5V \pm 0.2V, TA = -40°C to +125°C, see Figure 1)

Parameter	From (Input)	To (Output)		= 1.5V .1V) = 1.8V .15V	•) = 2.5V 0.2V) = 3.3V).3V		3) = 5V 3.5V	Unit
	(iliput)	(Output)	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
4	Α	В	2.0	19.7	2.0	17.6	1.3	9.4	1.1	6.9	0.9	5.3	20
t _{pLH}	В	Α	1.8	14.9	1.9	10.3	1.3	9.4	1.2	8.8	0.9	8.3	ns
4	Α	В	2.0	17.4	1.8	14.2	1.2	8.3	1.1	6.0	0.8	5.1	
t _{pHL}	В	Α	1.6	13.0	1.7	9.4	1.2	8.3	1.1	7.7	0.8	6.9	ns
t	DIR	Α	1.8	9.0	1.8	9.0	1.8	9.0	1.8	9.0	1.8	9.0	20
t _{pHZ}	DIR	В	2.7	24.8	2.7	23.6	2.2	12.1	2.5	10.3	2.0	7.6	ns
4	DIR	Α	1.5	6.4	1.5	6.4	1.5	6.4	1.5	6.4	1.5	6.4	no
t _{pLZ}	DIR	В	2.0	16.1	2.2	14.6	1.8	9.9	2.2	9.3	1.6	6.4	ns
4	DIR	Α	_	31.0	_	24.9	_	19.3	_	18.1	_	14.7	20
t _{pZH}	DIR	В	_	26.1	_	24.0	_	15.8	_	13.3	_	11.7	ns
4	DIR	Α	_	37.8	_	33.0	_	20.4	_	18.0	_	14.5	no
t _{pZL}	DIR	В	_	26.4	_	23.2	_	17.3	_	15.0	_	14.1	ns



Switching Characteristics (continued) (VCC (A) = 3.3V \pm 0.3V, TA = -40°C to +125°C, see Figure 1)

Parameter	From (Input)	To (Output)		= 1.5V .1V) = 1.8V .15V	•) = 2.5V 0.2V) = 3.3V).3V		3) = 5V).5V	Unit
	(Iliput)	(Output)	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
	Α	В	2.0	18.9	1.8	17.1	1.2	8.8	0.7	6.2	0.6	4.9	nc
t _{pLH}	В	Α	1.5	13.0	1.5	8.0	1.1	6.9	0.6	6.2	0.5	6.0	ns
4	Α	В	1.9	17.2	1.8	13.9	1.1	7.7	0.7	5.5	0.6	4.4	
t _{pHL}	В	Α	1.5	12.0	1.6	7.9	1.1	6.0	0.7	5.5	0.6	5.0	ns
A	DIR	Α	2.0	8.1	2.0	8.1	2.0	8.1	2.0	8.1	2.4	8.1	
t _{pHZ}	DIR	В	2.6	19.8	2.6	18.2	2.0	11.2	2.4	9.5	1.9	7.0	ns
4	DIR	Α	1.8	6.2	1.8	6.2	1.8	6.2	1.8	6.2	1.8	6.2	ns
tpLZ	DIR	В	2.0	15.0	2.1	13.8	1.7	8.6	2.0	7.9	1.5	5.4	115
4	DIR	Α	_	28.0	_	21.8	_	15.5	_	14.1	_	11.4	
t _{pZH}	DIR	В	_	25.1	_	23.3	_	15.0	_	12.4	_	11.1	ns
4	DIR	Α	_	31.8	_	26.1	_	17.2	_	15.0	_	12.0	200
t _{pZL}	DIR	В	_	25.3	_	22.0	_	15.8	_	13.6	_	12.5	ns

Switching Characteristics (continued) (V_{CC} (A) = 5.0V ± 0.5V, T_A = -40°C to +125°C, see Figure 1)

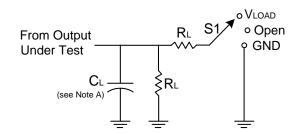
Parameter	From (Input)	To (Output)		= 1.5V .1V) = 1.8V .15V) = 2.5V 0.2V) = 3.3V).3V		3) = 5V).5V	Unit
	(Iliput)	(Output)	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
4	Α	В	1.9	18.3	1.7	16.7	0.9	8.3	0.6	6.0	0.4	4.3	20
t _{pLH}	В	Α	1.4	11.6	1.2	7.5	0.9	5.3	0.6	4.9	0.4	4.3	ns
4	Α	В	2.0	16.9	1.6	13.5	0.9	6.9	0.6	5.0	0.4	3.9	20
tpHL	В	Α	1.5	11.9	1.5	7.7	0.8	5.1	0.6	4.4	0.4	3.9	ns
t	DIR	Α	1.5	6.0	1.5	6.0	1.5	6.0	1.5	6.0	1.5	6.0	20
t _{pHZ}	DIR	В	2.6	19.1	2.6	17.8	2.0	10.7	2.4	8.8	2.2	6.3	ns
4	DIR	Α	1.2	4.1	1.2	4.1	1.1	4.1	0.9	4.1	0.8	4.1	20
t _{pLZ}	DIR	В	2.0	14.5	2.1	13.4	1.7	8.2	2.0	7.7	1.6	5.0	ns
4	DIR	Α	_	26.1	_	20.9	_	13.5	_	12.6	_	9.3	20
t pZH	DIR	В	_	22.4	_	20.8	_	12.4	_	10.1	_	8.4	ns
4	DIR	Α	_	31.0	_	25.5	_	15.8	_	13.2	_	10.2	no
t _{pZL}	DIR	В	_	22.9	_	19.5	_	12.9	_	11.0	_	9.9	ns

Operating Characteristics (T_A = +25°C, unless otherwise specified.)

Power Dis	Parameter sipation Capacitance	Test Conditions	Vcc(A) = Vcc(B) = 1.8V Typ	Vcc(A) = Vcc(B) = 2.5V Typ	Vcc(A) = Vcc(B) = 3.3V Typ	Vcc(A) = Vcc(B) = 5V Typ	Unit
	A- Input, B- Output	$C_L = 0pF$	3	4	4	4	
C _{pd} (A)	B- Input, A- Output	f = 10MHz $t_R = t_F = 1ns$	18	19	20	21	pF
	A- Input, B- Output	$C_L = 0pF$	18	19	20	21	
C _{pd} (B)	B- Input, A- Output	f = 10MHz $t_R = t_F = 1ns$	3	4	4	4	pF

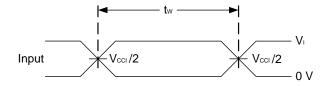


Parameter Measurement Information

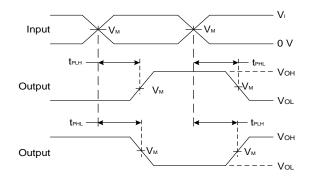


TEST	S1
tpLH/tpHL	Open
tpLz/tpzL	Vload
tpHZ/tpZH	GND

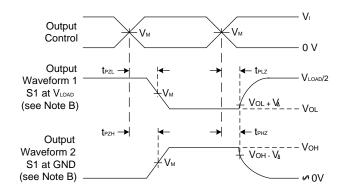
Van	Inputs		Voc	Vision	0.	D.	V/4
Vcc	Vı	t _R /t _F	Vм	VLOAD	CL	R∟	V Δ
1.8V±0.15V	V _{CCI}	≤2ns	V _{CCO} /2	2 X V _{CCO}	15pF	2ΚΩ	0.15V
2.5V±0.2V	Vcc	≤2ns	V _{CCO} /2	2 X V _{CCO}	15pF	2ΚΩ	0.15V
3.3V±0.3V	3V	≤2.5ns	V _{CCO} /2	2 X V _{CCO}	15pF	2ΚΩ	0.3V
5V±0.5V	Vcc	≤2.5ns	V _{CCO} /2	2 X V _{CCO}	15pF	2ΚΩ	0.3V



Voltage Waveform Pulse Duration



Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs



Voltage Waveform Enable and Disable Times Low and High Level Enabling

Figure 1 Load Circuit and Voltage Waveforms

Notes: 9. Includes test lead and test apparatus capacitance.

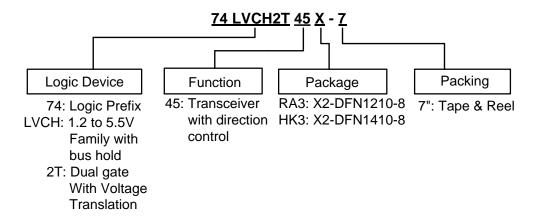
10. Waveform 1 is for an output with input set up as a low and device coming out or into 3-state via DIR control. Waveform 2 is for an output with input set up as a high and device coming out or into 3-state via DIR control.

11. All pulses are supplied at pulse repetition rate ≤ 10 MHz.

- 12. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
- 13. t_{PZL} and t_{PZH} are the same as t_{EN} .
- 14. t_{PLH} and t_{PHL} are the same as t_{PD}.
- 15. V_{CCI} is the V_{CC} associated with the input.
- 16. V_{CCO} is the V_{CC} associated with the output.



Ordering Information



Part Number	Dooksas Codo	Dookoaina	7" Tape and Reel (Note 7)	
	Package Code	Packaging	Quantity	Part Number Suffix
74LVCH2T45RA3-7	RA3	X2-DFN1210-8	5000/Tape & Reel	-7
74LVCH2T45HK3-7	HK3	X2-DFN1410-8	5000/Tape & Reel	-7

Note: 17. The taping orientation is located on our website at http://www.diodes.com/package-outlines.html.

Marking Information

(1) X2-DFN1210-8

(Top View)

XX $\underline{Y} \underline{W} \underline{X}$ XX: Identification Code

Y: Year: 0~9

<u>W</u>: Week: A~Z: 1~26 week; a~z: 27~52 week; z represents

52 and 53 week

X: Internal Code

Part Number	Package	Identification Code	
74LVCH2T45RA3-7	X2-DFN1210-8	4C	

(2) X2-DFN1410-8

(Top View)



XX: Identification Code

Y: Year: 0~9

<u>W</u>: Week: A~Z: 1~26 week; a~z: 27~52 week; z represents

52 and 53 week X: Internal Code

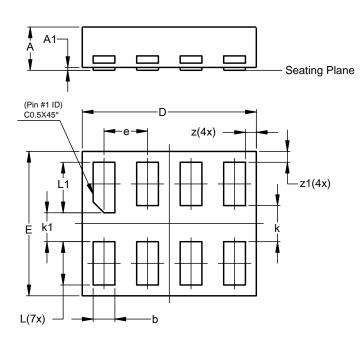
Part Number	Package	Identification Code	
74LVCH2T45HK3-7	X2-DFN1410-8	4D	



Package Outline Dimensions

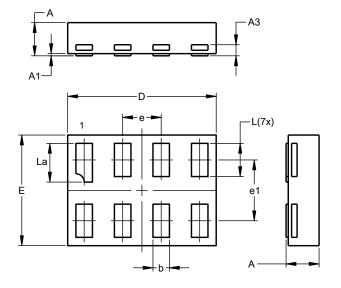
Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN1210-8



X2-DFN1210-8			
Dim	Min	Max	Тур
Α	-	0.35	0.30
A1	0	0.03	0.02
b	0.10	0.20	0.15
D	1.15	1.25	1.20
Е	0.95	1.05	1.00
е	-	-	0.30
k	-	-	0.25
k1	-	-	0.20
١	0.25	0.35	0.30
L1	0.30	0.40	0.35
Z	0.050	0.100	0.075
z1	0.050	0.100	0.075
All Dimensions in mm			

X2-DFN1410-8



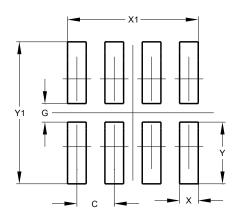
X2-DFN1410-8				
Dim	Min	Max	Тур	
Α	0.30	0.35	0.33	
A1	0.00	0.03	0.02	
A3	-		0.10	
b	0.12	0.20	0.15	
D	1.30	1.40	1.35	
Е	0.95	1.05	1.00	
е			0.35	
e1			0.55	
L	0.27	0.35	0.30	
L1	0.32	0.40	0.35	
All Dimensions in mm				



Suggested Pad Layout

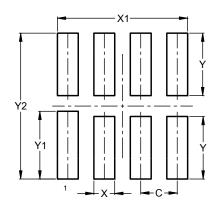
Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN1210-8



Dimensions	Value (in mm)
С	0.300
G	0.150
Х	0.150
X1	1.050
Υ	0.500
Y1	1.150

X2-DFN1410-8



Dimensions	Value	
Dillielisions	(in mm)	
С	0.350	
Х	0.200	
X1	1.250	
Υ	0.600	
Y1	0.650	
Y2	1.400	

Mechanical Data

X2-DFN1210-8

- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu Nickel Palladium Gold, Solderable per MIL-STD-202, Method 208@4
- Weight: 0.002 grams (Approximate)

X2-DFN1410-8

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